

IN THE CLAIMS:

1. (Currently Amended) A semiconductor light emitting device comprising:

a multilayer epitaxial structure including a first conductive layer, a second conductive layer, and a light emitting layer between the first conductive layer and the second conductive layer, a main surface of the second conductive layer which faces away from the light emitting layer being a light extraction surface;

a first electrode formed on a main surface of the first conductive layer which faces away from the light emitting layer;

a second electrode formed on the main surface of the second conductive layer which faces away from the light emitting layer;

a first power supply terminal that is electrically connected to the first electrode and forms at least part of a metal layer, the multilayer epitaxial structure being formed on the metal layer in such a manner that the first conductive layer is closer to the metal layer than the second conductive layer is, the metal layer supporting the multilayer epitaxial structure, and conducting heat generated in the light emitting layer; and

a second power supply terminal that is electrically connected to the second electrode by means of a conductive member which extends from the second electrode in a direction parallel to the main surface of the second conductive layer,

wherein the second power supply terminal forms a conductive film on a surface of the metal layer on which the multilayer epitaxial structure is formed, and an insulating film is formed between the second power supply terminal and the surface of the metal layer.

2. (Original) The semiconductor light emitting device of Claim 1, wherein
the metal layer is electrically divided into at least two portions, and
at least one of the portions is constituted as the first power supply terminal, and at
least one of a rest of the portions is connected to the second electrode, to be constituted as the
5 second power supply terminal.

3. (Cancelled)

4. (Currently Amended) The semiconductor light emitting device of Claim [[3]] 1,
wherein
the first power supply terminal forms the entire metal layer.

5. (Currently Amended) The semiconductor light emitting device of Claim [[3]] 1,
wherein
the conductive film is formed so as to surround the multilayer epitaxial structure,
and is also constituted as a light-reflective film.

6. (Original) The semiconductor light emitting device of Claim 1, wherein
the first electrode is formed on substantially the entire main surface of the first
conductive layer which faces away from the light emitting layer, and reflects light emitted from
the light emitting layer.

7. (Original) The semiconductor light emitting device of Claim 1, wherein
the second electrode is a transparent electrode which transmits the light emitted
from the light emitting layer.

8. (Original) The semiconductor light emitting device of Claim 7, wherein
the second electrode is formed on substantially the entire main surface of the
second conductive layer which faces away from the light emitting layer.

9. (Original) The semiconductor light emitting device of Claim 1, further
comprising:

a phosphor layer formed on the multilayer epitaxial structure so as to cover the
main surface of the second conductive layer which faces away from the light emitting layer, the
5 phosphor layer including a light emitting substance which is excited by the light emitted from the
light emitting layer, to emit light.

10. (Original) The semiconductor light emitting device of Claim 1, wherein
each of the first conductive layer, the light emitting layer, and the second
conductive layer is made of a compound semiconductor including nitrogen.

11. (Currently Amended) A semiconductor light emitting device comprising:
a light emitting element array formed in such a manner that a plurality of light
emitting elements are connected in series, each of the plurality of light emitting elements
including: (a) a multilayer epitaxial structure including a first conductive layer, a second
5 conductive layer and a light emitting layer between the first conductive layer and the second
conductive layer, a main surface of the second conductive layer which faces away from the light
emitting layer being a light extraction surface, (b) a first electrode formed on a main surface of
the first conductive layer which faces away from the light emitting layer, and (c) a second
electrode formed on the main surface of the second conductive layer which faces away from the

10 light emitting layer, the first electrode and the second electrode are positioned to each other in a same manner for each light emitting element; and

a metal layer on which the light emitting element array is formed, with an insulating layer therebetween, in such a manner that the first electrode is positioned closer to the metal layer than the second electrode is, the metal layer connecting and supporting the multilayer epitaxial structures and conducting heat generated in the light emitting layer, wherein

the metal layer is electrically divided into at least two portions,

at least one of the portions is connected to a first electrode of a light emitting element at one end of the light emitting element array, to be constituted as a first power supply terminal, and

20 at least one of a rest of the portions is connected to a second electrode of a light emitting element at the other end of the light emitting element array, by means of a conductive member which extends from the second electrode in a direction parallel to a main surface of a second conductive layer of the light emitting element, to be constituted as a second power supply terminal,

25 wherein the multilayer epitaxial structure being formed on the metal layer in such a manner that the first conductive layer is closer to the metal layer than the second conductive layer is, the metal layer supporting the multilayer epitaxial structure, and conducting heat generated in the light emitting layer.

12. (Original) The semiconductor light emitting device of Claim 11, wherein
the first electrode is formed on substantially the entire main surface of the first
conductive layer which faces away from the light emitting layer, and reflects light emitted from
the light emitting layer.

13. (Original) The semiconductor light emitting device of Claim 11, wherein
the second electrode is a transparent electrode which transmits the light emitted
from the light emitting layer.

14. (Original) The semiconductor light emitting device of Claim 13, wherein
the second electrode is formed on substantially the entire main surface of the
second conductive layer which faces away from the light emitting layer.

15. (Original) The semiconductor light emitting device of Claim 11, further
comprising:

a phosphor layer formed on the multilayer epitaxial structure so as to cover the
main surface of the second conductive layer which faces away from the light emitting layer, the
5 phosphor layer including a light emitting substance which is excited by the light emitted from the
light emitting layer, to emit light.

16. (Original) The semiconductor light emitting device of Claim 11, wherein
each of the first conductive layer, the light emitting layer, and the second
conductive layer is made of a compound semiconductor including nitrogen.

17. (Previously Presented) A lighting module comprising:
a printed wiring board including a bonding pad; and
a semiconductor light emitting device as defined in Claim 1, the semiconductor
light emitting device being mounted on the printed wiring board by connecting a metal layer
5 included in the semiconductor light emitting device to the bonding pad.

18 (Original) A lighting apparatus comprising a lighting module as defined in Claim
17.

19.-28. (Cancelled)

29. (New) The semiconductor light emitting device of Claim 2, wherein
the first power supply terminal forms the entire metal layer.
30. (New) The semiconductor light emitting device of Claim 2, wherein
the conductive film is formed so as to surround the multilayer epitaxial structure,
and is also constituted as a light-reflective film.
31. (New) The semiconductor light emitting device of Claim 2, wherein
the first electrode is formed on substantially the entire main surface of the first
conductive layer which faces away from the light emitting layer, and reflects light emitted from
the light emitting layer.
32. (New) The semiconductor light emitting device of Claim 2, wherein
the second electrode is a transparent electrode which transmits the light emitted
from the light emitting layer.

33. (New) The semiconductor light emitting device of Claim 32, wherein
the second electrode is formed on substantially the entire main surface of the
second conductive layer which faces away from the light emitting layer.

34. (New) The semiconductor light emitting device of Claim 2, further comprising:
a phosphor layer formed on the multilayer epitaxial structure so as to cover the
main surface of the second conductive layer which faces away from the light emitting layer, the
phosphor layer including a light emitting substance which is excited by the light emitted from the
5 light emitting layer, to emit light.

35. (New) The semiconductor light emitting device of Claim 2, wherein
each of the first conductive layer, the light emitting layer, and the second
conductive layer is made of a compound semiconductor including nitrogen.

36. (New) A lighting module comprising:
a printed wiring board including a bonding pad; and
a semiconductor light emitting device as defined in Claim 2, the semiconductor
light emitting device being mounted on the printed wiring board by connecting a metal layer
5 included in the semiconductor light emitting device to the bonding pad.

37. (New) A lighting apparatus comprising a lighting module as defined in Claim 36.

38. (New) A lighting module comprising:
- a printed wiring board including a bonding pad; and
- a semiconductor light emitting device as defined in Claim 11, the semiconductor
- light emitting device being mounted on the printed wiring board by connecting a metal layer
- 5 included in the semiconductor light emitting device to the bonding pad.
39. (New) A lighting apparatus comprising a lighting module as defined in Claim 38.